

b1
wml
forming a lower conducting film over a substrate by sputtering; and
forming an upper conducting film directly on and in contact with said lower
conducting film by CVD.

3. (Twice Amended) A method for fabricating a semiconductor device
including a capacitor device having a lower electrode, a capacitor dielectric film formed on said
lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a
step of:

b2
forming a conducting film to be formed into said upper electrode including sub-
steps of:

forming a lower conducting film over said capacitor dielectric film by sputtering;
and

forming an upper conducting film directly on and in contact with said lower
conducting film by CVD.

8. (Amended) The method for fabricating a semiconductor device of
Claim 1,

b3
wherein said capacitor device is a concaved capacitor device, and

wherein said lower conducting film is formed over an insulating film having a
recess formed over said substrate.